

CMLDM7484

**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET**



SOT-563 CASE

APPLICATIONS:

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Devices

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current
Power Dissipation (Note 1)
Power Dissipation (Note 2)
Power Dissipation (Note 3)
Operating and Storage Junction Temperature
Thermal Resistance (Note 1)

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS
I_{GSSF}, I_{GSSR}	$V_{GS}=8.0\text{V}, V_{DS}=0$
I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$
BV_{DSS}	$V_{GS}=0, I_D=10\mu\text{A}$
BV_{DSS}	$V_{GS}=0, I_D=100\mu\text{A}$
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
V_{SD}	$V_{GS}=0, I_S=400\text{mA}$
V_{SD}	$V_{GS}=0, I_S=100\text{mA}$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=200\text{mA}$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=430\text{mA}$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=100\text{mA}$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=200\text{mA}$
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=75\text{mA}$
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=100\text{mA}$

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM7484 consists of complementary N-Channel and P-Channel enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: 8C7

FEATURES:

- ESD Protection up to 2kV
- 350mW Power Dissipation
- Very Low $r_{DS(ON)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, SOT-563 Surface Mount Package

SYMBOL

SYMBOL		UNITS
V_{DS}	30	V
V_{GS}	8.0	V
I_D	450	mA
P_D	350	mW
P_D	300	mW
P_D	150	mW
T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Θ_{JA}	357	$^{\circ}\text{C/W}$

N-CH (Q1)

MIN	MAX
-	3.0
-	1.0

P-CH (Q2)

MIN	MAX
-	3.0
-	1.0

UNITS

μA
μA
V
V
V
V
V
Ω
Ω
Ω
Ω
Ω
Ω

R4 (28-January 2014)

CMLDM7484

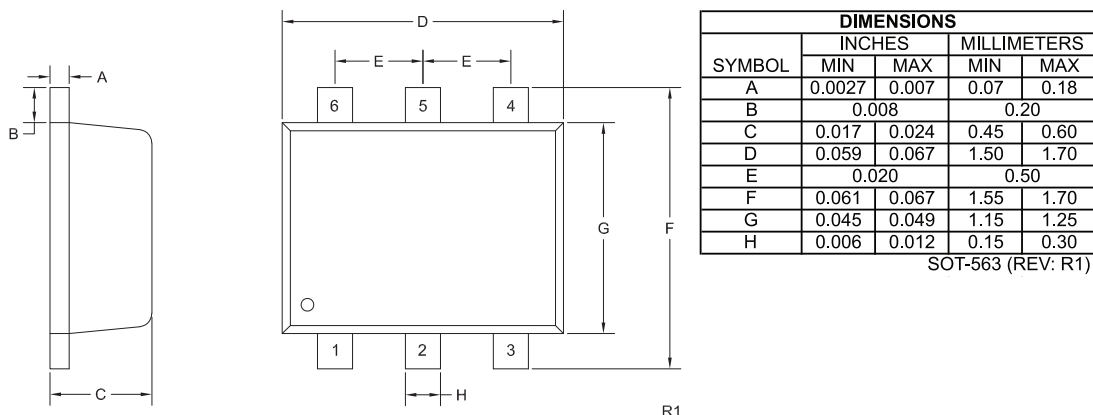
**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET**



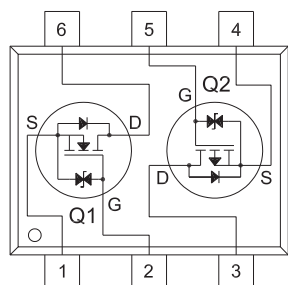
ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	N-CH (Q1)			P-CH (Q2)			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
g _{FS}	$V_{DS}=10\text{V}$, $I_D=100\text{mA}$	200	-	-	200	-	-	mS
C _{rss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	-	-	10	-	-	10	pF
C _{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	-	-	45	-	-	55	pF
C _{oss}	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$	-	-	15	-	-	15	pF
Q _{g(tot)}	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	0.792	-	-	-	-	nC
Q _{g(tot)}	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	-	-	-	0.88	-	nC
Q _{gs}	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	0.15	-	-	-	-	nC
Q _{gs}	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	-	-	-	0.35	-	nC
Q _{gd}	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	0.23	-	-	-	-	nC
Q _{gd}	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$	-	-	-	-	0.128	-	nC

SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

MARKING CODE: 8C7

R4 (28-January 2014)